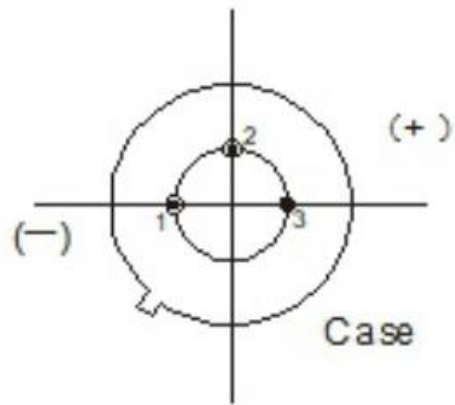
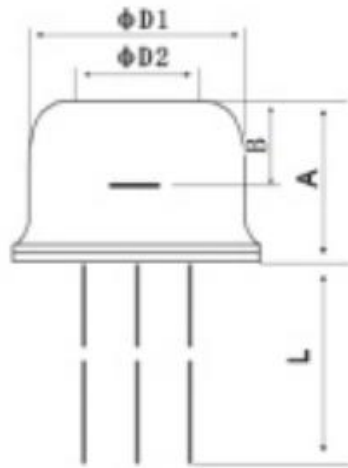


特性参数 Parameter	符号 Symbol	测试条件 Test Condition	最小 Min.	典型 Typ.	最大 Max.	单位 Unit
光谱响应范围 Response Spectrum	λ	—	1100 ~ 1680			nm
光敏面直径 Active Diameter	ϕ	—	80			μm
响应度 Responsivity	Re	$\lambda=1310\text{nm}, V=-1\text{V}, P_o=1\mu\text{W}$	0.90	0.95	—	A/W
		$\lambda=1550\text{nm}, V=-1\text{V}, P_o=1\mu\text{W}$	0.95	1.00	—	A/W
正向电压 Forward Voltage	V_f	$I_f=1\text{mA}$	—	0.57	—	V
饱和光功率 Saturated Optical Power	P_{sat}	$V=-5\text{V}$	10	—	—	dBm
暗电流 Dark Current	I_d	$V=-5\text{V}$	—	0.40	—	nA
反向击穿电压 Reverse Breakdown Voltage	V_{BR}	$I_d=10\mu\text{A}$	40	—	—	V
电容 Capacitance	C	$V=-5\text{V}, f=1\text{MHz}$	—	0.45	0.55	pF
-3dB 截止频率 -3dB cut-off frequency	BW	$\lambda=1310\text{nm}, V=-5\text{V}$ $R_L=50\Omega$	2	—	—	GHz
二阶交调失真 Second Order Intermodulation Distortion	IMD2	$V=-5\text{V}$ $P_o=1\text{mW}, \text{OMI}=40\%, \lambda=1550\text{nm},$ $R_L=50\Omega$	—	—	-65	dBc
三阶交调失真 Third Order Intermodulation Distortion	IMD3		—	—	-75	dBc



PIN 1: Cathode

PIN 2: Gnd

PIN 3: Anode

PIN 1: Anode

PIN 2: Gnd

PIN 3: Cathode

